

# **Hex Buffer(Open Drain)**

#### **Features**

HIGH SPEED:

 $t_{PD}$  = 6ns (TYP.) at  $V_{CC}$  = 6V

• LOW POWER DISSIPATION:

 $I_{CC} = 1\mu A(MAX.)$  at  $T_A=25$ °C

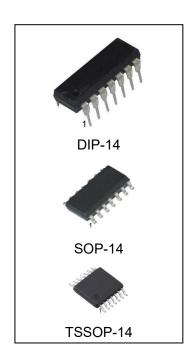
• HIGH NOISE IMMUNITY:

 $V_{NIH} = V_{NIL} = 28 \% V_{CC} (MIN.)$ 

• WIDE OPERATING VOLTAGE RANGE:

 $V_{CC}$  (OPR) = 2V to 6V

PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 07



## **Ordering Information**

DEVICE	Package Type	MARKING	Packing	Packing Qty
HG74HC07N	DIP-14	HG74HC07	TUBE	1000pcs/box
HG74HC07M/TR	SOP-14	HG74HC07	REEL	2500pcs/reel
HG74HC07MT/TR	TSSOP-14	H74HC07	REEL	2500pcs/reel



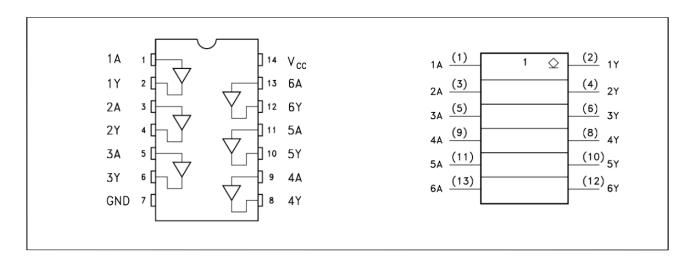
### **DeScription**

The HG74HC07 is an high speed CMOS HEX OPEN DRAIN BUFFER fabricated with silicon gate C<sup>2</sup>MOS technology.

The internal circuit is composed of 2 stages including buffer output, which enables high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

### **Pin Connection And lec Logic Symbols**



## **Pin Description**

PIN No	SYMBOL	NAME AND FUNCTION
1, 3, 5, 9,11,13	1A to 6A	Data Inputs
2, 4, 6, 8,10,12	1Y to 6Y	Data Outputs
7	GND	Ground (0V)
14	V <sub>CC</sub>	Positive Supply Voltage

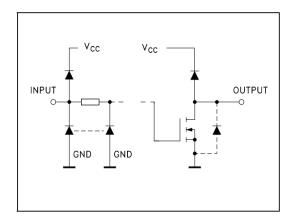
#### **Truth Table**

A	Y
L	L
Н	Z

ZZ:High Impedance



## **Input And Output Equivalent Circuit**



## **Absolute Maximum Ratings**

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to VCC + 0.5	V
Vo	DC Output Voltage	-0.5 to VCC + 0.5	V
ΙΚ	DC Input Diode Current	20	mA
lok	DC Output Diode Current	20	mA
IO	DC Output Current	25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC VCC or Ground Current	50	mA
PD	Power Dissipation	500(*)	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10s)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(\*) 500mW at 65°C; derate to 300mW by 10mW/°C from 65°Cto 85°C

## **Recommended Opera Ting Conditions**

Symbol	Parameter		Value	Unit
Vcc	Supply Voltage		2 to 6	٧
VI	Input Voltage		0 to VCC	٧
Vo	Output Voltage	0 to VCC	V	
Top	Operating Temperature		-40 to 85	°C
		VCC = 2.0V	0 to 1000	ns
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	V <sub>C</sub> C = 4.5V	0 to 500	ns
		0 to 400	ns	



## **Dc Specifications**

		Те	st Condition			Value			
Symbol	Parameter	V <sub>CC(V)</sub>			TA = 25°C		-40 to	85°C	Unit
		*CC(V)		Min	Тур	Max	Min	Max	
	VIH High Level Input Voltage	2.0		1.5			1.5		
VIH		4.5		3.15			3.15		V
Voltage	Voltage	6.0		4.2			4.2		
Low Lovel Input	2.0				0.5		0.5		
VIL	Low Level Input IL Voltage	4.5				1.35		1.35	V
Voltage	Voltage	6.0				1.8		1.8	
		2.0	IO=20μA		0.0	0.1		0.1	
		4.5	ΙΟ=20μΑ		0.0	0.1		0.1	
VOL	Low Level Output Voltage	6.0	IO=20μA		0.0	0.1		0.1	V
	Voltage	4.5	IO=4.0 mA		0.17	0.26		0.33	
		6.0	IO=5.2 mA		0.18	0.26		0.33	
lį	Input Leakage Current	6.0	VI=VCC or GND			0.1		1	μA
loz	Output Leakage Current	6.0	VI = VIH or VILVO=VCC or			0.5		5	μA
lcc	Quiescent Supply Current	6.0	V <sub>I</sub> = V <sub>C</sub> C or GND			1		10	μA

## **AC Electrical Characteristics**(CL=5pF,Input tr=tf=6ns)

		Tes	st Condition			Value				
Symbol	Parameter	Vocan			TA = 25°0		-40 to	85°C	Unit	
		VCC(V)		Min.	Тур.	Max.	Min.	Max.		
	t <sub>THL</sub> Output Transition Time	2.0			30	75		95		
tTHL			4.5			8	15		19	ns
		6.0			7	13		16		
		2.0			10	90		115		
tPLZ	Propagation Delay	4.5	$R_L = 1 K\Omega$		7	18		23	ns	
	Timo	6.0			6	15		20		
		2.0			17	90		115		
tPZL Propagation Delay Time	4.5	RL = 1 KΩ		7	18		23	ns		
	11110	6.0			5	15		20		

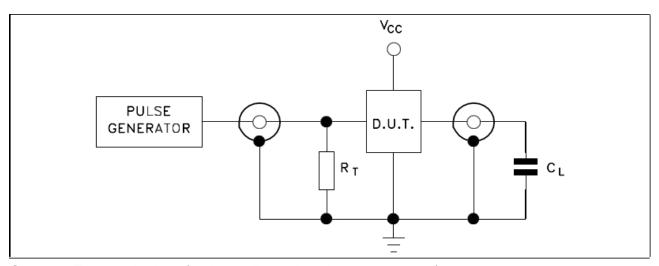


### **Capacitive Charactristics**

		Test Condition								
Symbol	Parameter	V <sub>CC</sub> (V)			Т	T <sub>A</sub> = 25°C			-40 to 85°C	
		*CC(V)		Min.	Тур.	Max.	Min.	Max.		
C <sub>IN</sub>	Input Capacitance	5.0				5	10		10	pF
COUT	Output Capacitance	5.0				3				pF
CPD	Power Dissipation Capacitance (note1)	5.0				4				pF

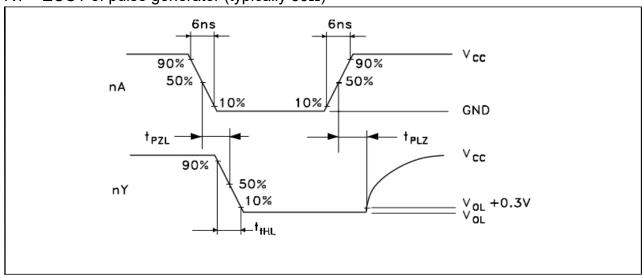
 $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/6$  (per gate)

#### **Test Circuit**



CL = 50pF or equivalent (includes jig and probe capacitance)

RT = ZOUT of pulse generator (typically  $50\Omega$ )

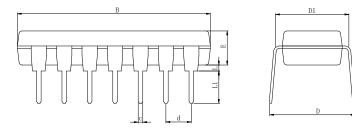


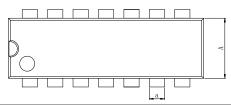
WAVEFORM:PROPAGA TION DELAY TIME(f=1MHz;50% duty cycle)



## **Physical Dimensions**

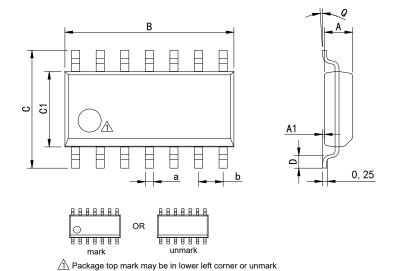
### DIP-14





Dimensions In Millimeters(DIP-14)											
Symbol:	Α	В	D	D1	Е	L	L1	а	С	d	
Min:	6.10	18.94	8.10	7.42	3.10	0.50	3.00	1.50	0.40	2.54.000	
Max:	6.68	19.56	10.9	7.82	3.55	0.70	3.60	1.55	0.50	2.54 BSC	

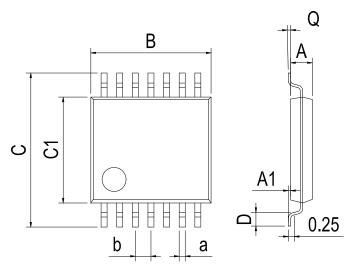
#### SOP-14



Dimensions In Millimeters(SOP-14)										
Symbol:	Α	A1	В	С	C1	D	Q	а	p	
Min:	1.35	0.05	8.55	5.80	3.80	0.40	0°	0.35	1 27 DCC	
Max:	1.55	0.20	8.95	6.20	4.00	0.80	8°	0.45	1.27 BSC	



## TSSOP-14



Dimensions In Millimeters(TSSOP-14)										
Symbol:	Α	A1	В	С	C1	D	Q	а	b	
Min:	0.85	0.05	4.90	6.20	4.30	0.40	0°	0.20	0.65 BSC	
Max:	0.95	0.20	5.10	6.60	4.50	0.80	8°	0.25	0.00 600	



## **Revision History**

REVISION NUMBER	DATE	REVISION	PAGE
V1.0	2019-3	New	1-9
V1.1	2023-9	Modify features ang descriptions、Update encapsulation type、Updated DIP-14 Physical dimension、Update Title	1、4、6
V1.2	2024-10	Update Lead Temperature	3
V1.3	2025-9	Update important statements、Update sop-14 Dimension drawing	6、9



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